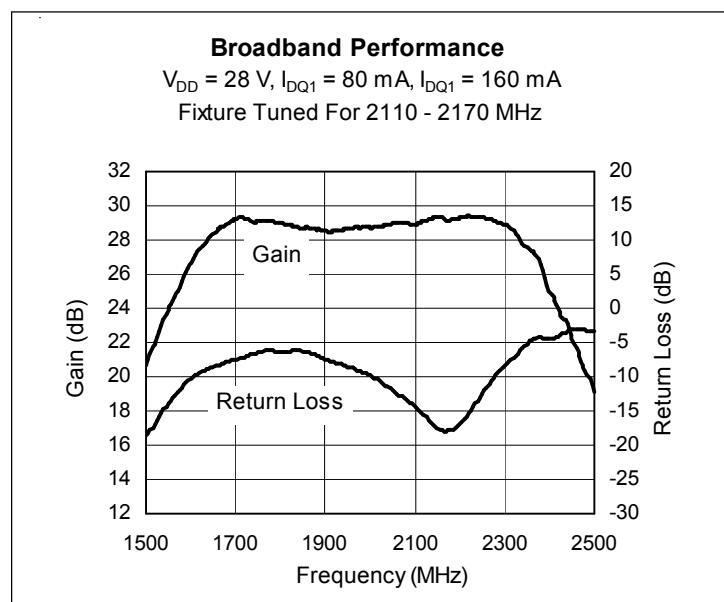


Wideband RF LDMOS Integrated Power Amplifier 15 W, 1800 – 2200 MHz

Description

The PTMA210152M is a wideband, matched, 15-watt, 2-stage LDMOS integrated amplifier intended for wideband driver applications in the 1800 to 2200 MHz band. This device is offered in a 20-lead thermally-enhanced overmolded package for cool and reliable operation.

PTMA210152M
Package PG-DSO-20-63



Features

- Designed for wide RF bandwidth and low memory effects
- Broadband input on-chip matching
- Typical two-carrier WCDMA performance at 2140 MHz, 28 V, 7 W avg.
 - Gain = 28.5 dB
 - Efficiency = 33 %
 - IMD3 = -32 dBc
- Typical CW performance, 2140 MHz, 28 V
 - Output power at P-1dB ~ 20 W
 - Efficiency > 49%
- Integrated ESD protection. Meets HBM Class 1B (minimum), per JESD22-A114F
- Capable of handling 10:1 VSWR @ 28 V, 15 W (CW) output power
- Thermally-enhanced RoHS-compliant package

RF Characteristics

Two-carrier WCDMA Measurements (not subject to production test—verified by design/characterization in Infineon test fixture)

$V_{DS} = 28\text{ V}$, $I_{DQ1} = 80\text{ mA}$, $I_{DQ2} = 160\text{ mA}$, $f = 2110 - 2170\text{ MHz}$, $P_{OUT} = 7\text{ W}$ average

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	G_{ps}	—	28.5	—	dB
Power Added Efficiency	η	—	33	—	%
Input Return Loss	IRL	—	-14	—	dB
Adjacent Channel Power Ratio	ACPR	—	-36	—	dBc
Intermodulation Distortion	IMD3	—	-32	—	dBc

table continued next page

All published data at $T_{CASE} = 25^\circ\text{C}$ unless otherwise indicated

ESD: Electrostatic discharge sensitive device—observe handling precautions!

RF Characteristics (cont.)

Two-carrier WCDMA Measurements (cont.)

$V_{DS} = 28\text{ V}$, $I_{DQ1} = 80\text{ mA}$, $I_{DQ2} = 160\text{ mA}$, $f = 2110 - 2170\text{ MHz}$, $P_{OUT} = 7\text{ W}$ average

Characteristic	Symbol	Min	Typ	Max	Unit
Spurs Load 3:1	—	—	−60	—	dBc
Gain Flatness	ΔG	—	0.43	—	dB

Two-tone Measurements (tested in Infineon test fixture)

$V_{DD} = 28\text{ V}$, $I_{DQ1} = 80\text{ mA}$, $I_{DQ2} = 160\text{ mA}$, $P_{OUT} = 15\text{ W PEP}$, $f = 2140\text{ MHz}$, tone spacing = 1 MHz

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	G_{ps}	27.5	28.5	30	dB
Drain Efficiency	η_D	33	34	—	%
Intermodulation Distortion	IMD	—	−33	−30	dBc
Input Return Loss		—	−14	−10	dB

DC Characteristics

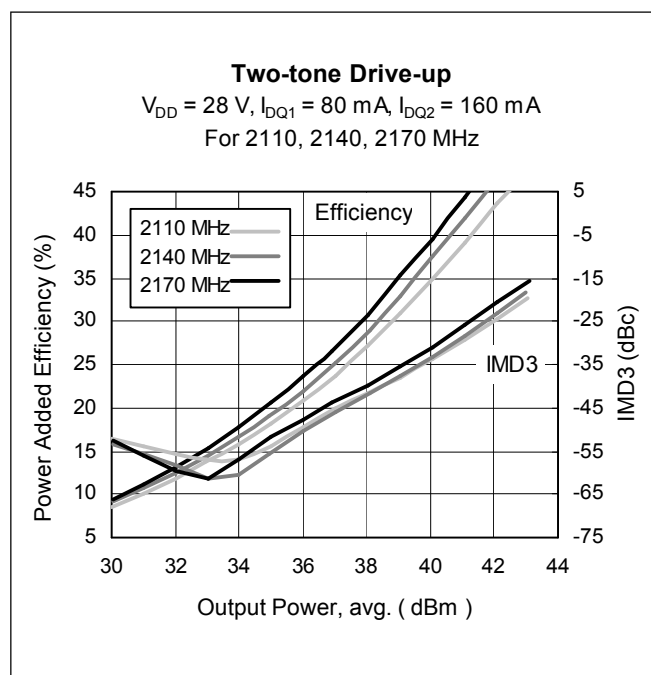
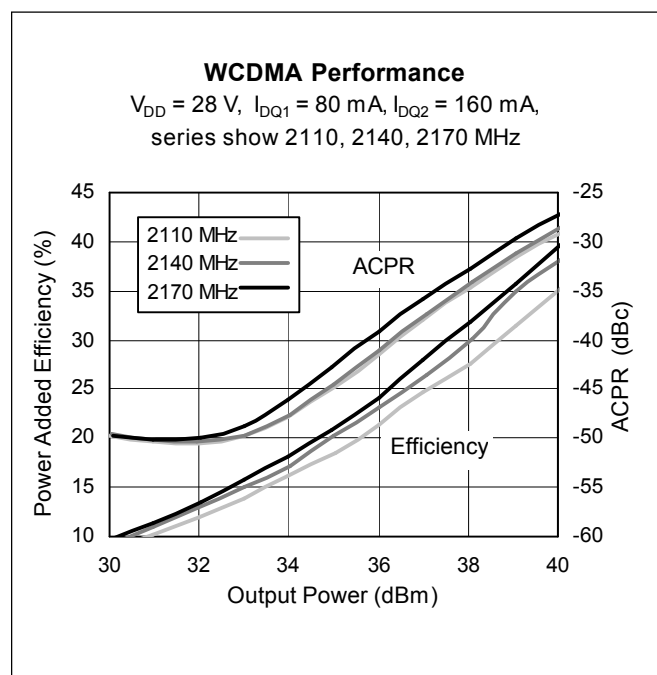
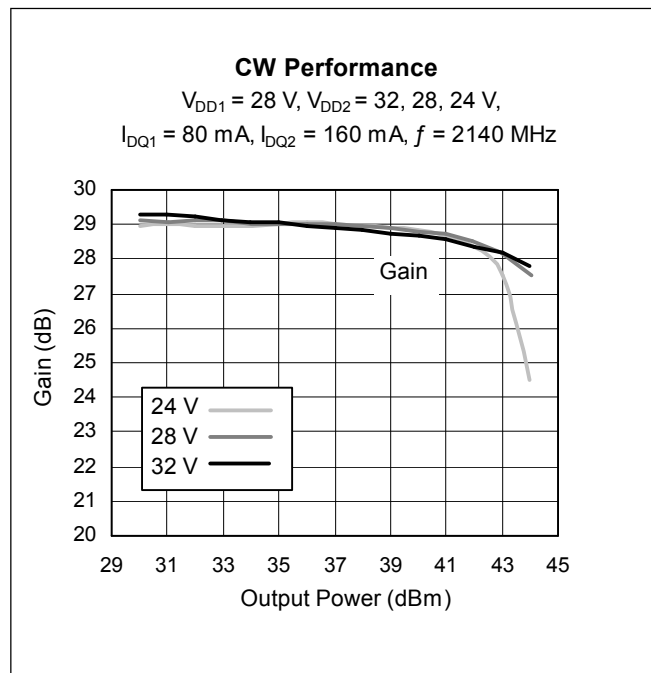
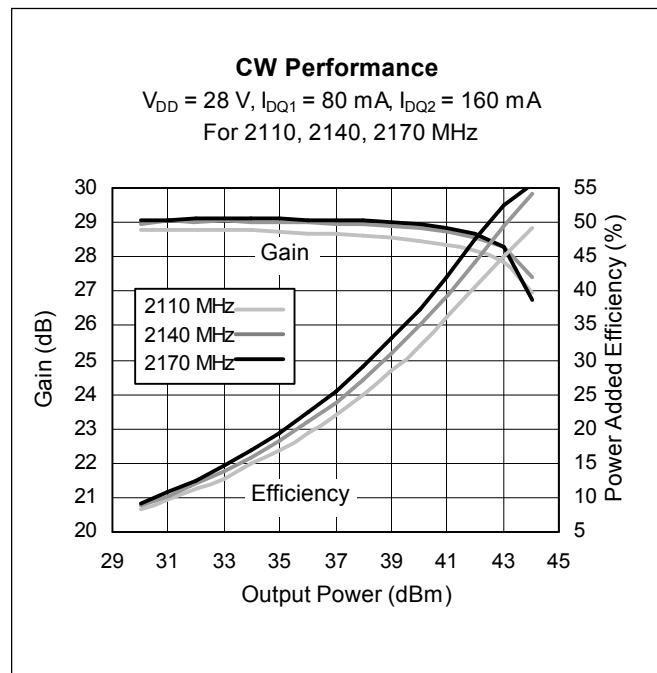
Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$, $I_{DS} = 10\text{ mA}$	$V_{(BR)DSS}$	65	—	—	V
Drain Leakage Current	$V_{DS} = 28\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	1.0	μA
	$V_{DS} = 63\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	10.0	μA
On-State Resistance	Stage 1 $V_{GS} = 10\text{ V}$, $V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	0.6	—	Ω
	Stage 2 $V_{GS} = 10\text{ V}$, $V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	3.5	—	Ω
Operating Gate Voltage	$V_{DS} = 28\text{ V}$	V_{GS}	2	2.5	3	V
Gate Leakage Current	$V_{GS} = 10\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	—	—	1.0	μA

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	65	V
Gate-Source Voltage	V_{GS}	-0.5 to +12	V
Junction Temperature	T_J	200	°C
Input Power	P_{IN}	15	dBm
Total Device Dissipation	P_D	70	W
Above 25°C derate by		0.4	W/°C
Storage Temperature Range	T_{STG}	-40 to +150	°C
Thermal Resistance ($T_{CASE} = 70^\circ\text{C}$, 15 W CW)	Stage 1	$R_{\theta JC}$	10.7 °C/W
	Stage 2	$R_{\theta JC}$	2.9 °C/W

Ordering Information

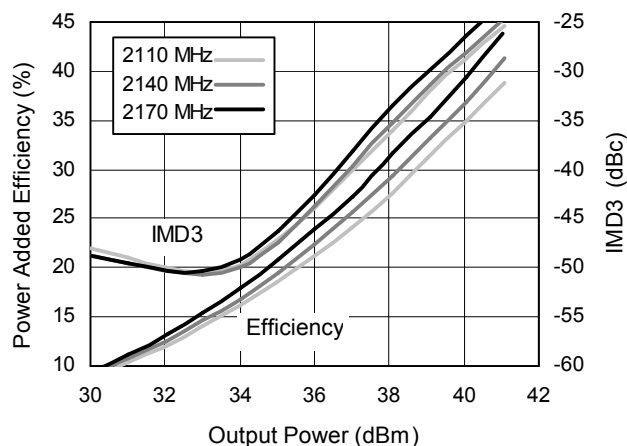
Type and Version	Package Outline	Package Description	Shipping
PTMA210152M V1	PG-DSO-20-63	Thermally-enhanced surface-mount	Tape

Typical Performance at 2140 MHz (data taken in a production test fixture)


Typical Performance at 2140 MHz (cont.)

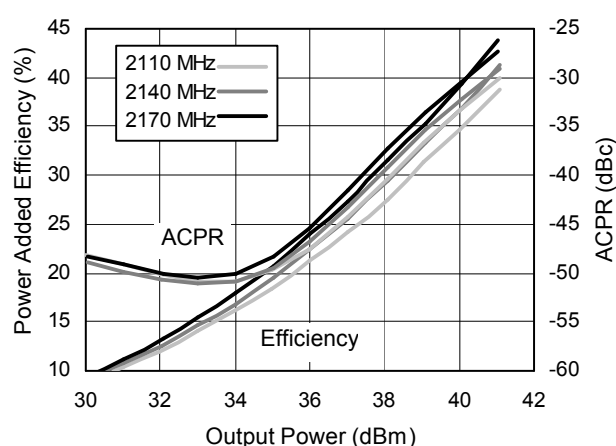
Two-carrier WCDMA Performance

$V_{DD} = 28\text{ V}$, $I_{DQ1} = 80\text{ mA}$, $I_{DQ2} = 160\text{ mA}$,
series show 2110, 2140, 2170 MHz



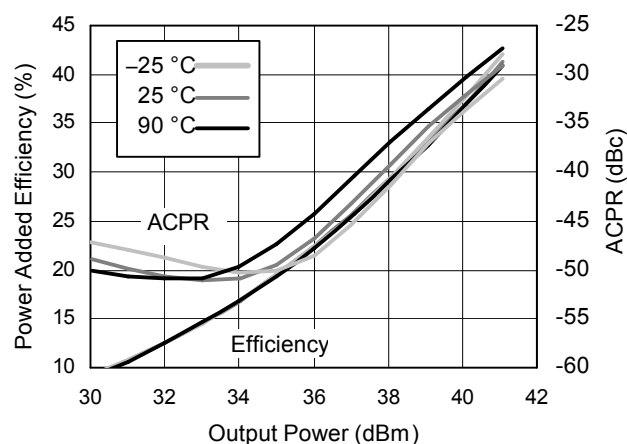
Two-carrier WCDMA Performance

$V_{DD} = 28\text{ V}$, $I_{DQ1} = 80\text{ mA}$, $I_{DQ2} = 160\text{ mA}$,
series show 2110, 2140, 2170 MHz



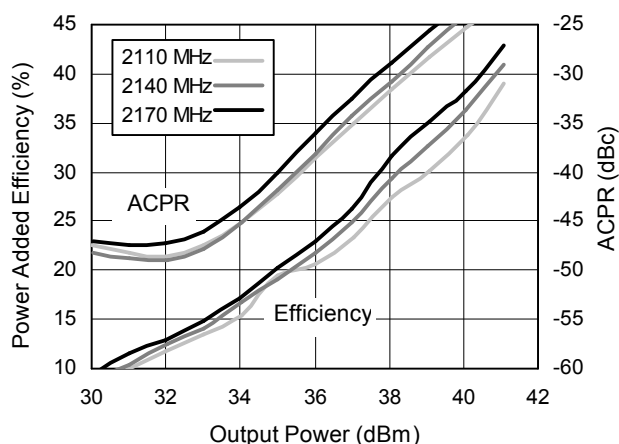
Two-carrier WCDMA Performance

$V_{DD} = 28\text{ V}$, $I_{DQ1} = 80\text{ mA}$, $I_{DQ2} = 160\text{ mA}$,
series show 2140 MHz at various temperatures

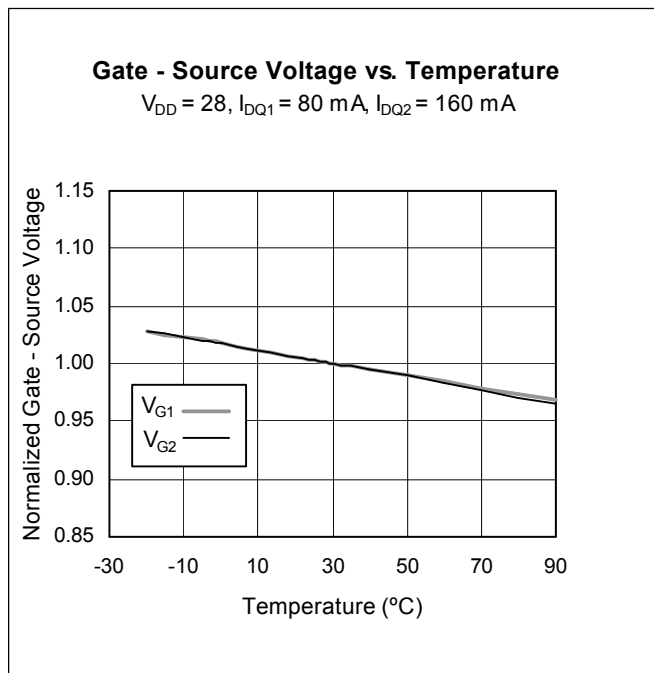


Six-carrier TD-SCDMA Performance

$V_{DD} = 28\text{ V}$, $I_{DQ1} = 80\text{ mA}$, $I_{DQ2} = 160\text{ mA}$,
series show 2110, 2140, 2170 MHz

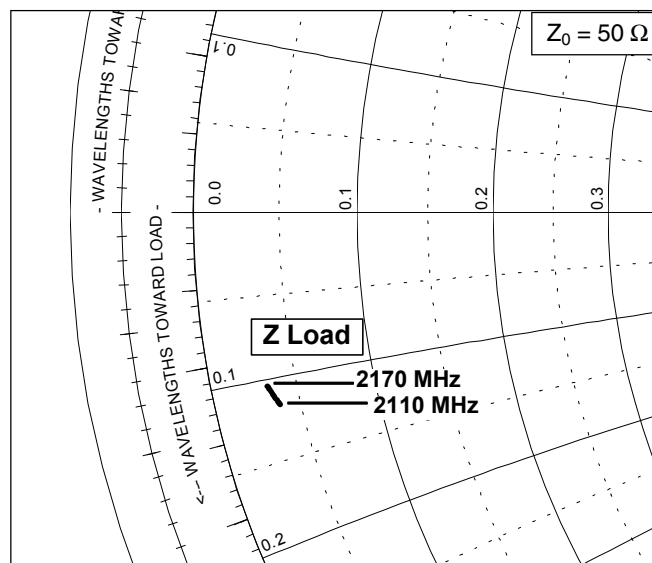
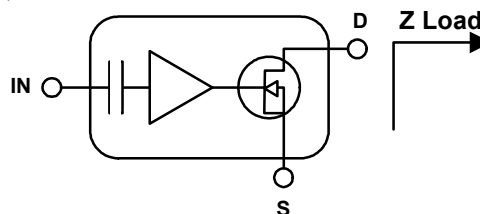


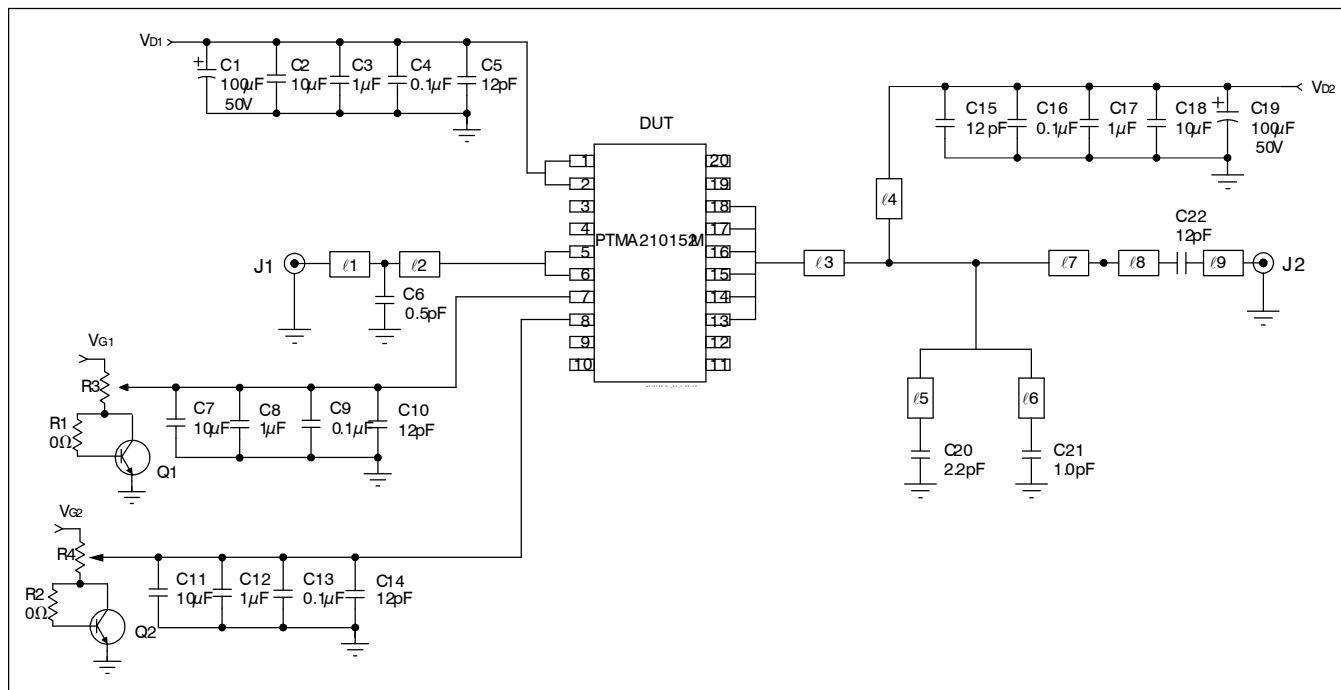
Typical Performance at 2140 MHz (cont.)



Broadband Circuit Impedance (2140 MHz test circuit)

Frequency MHz	Z Load W	
	R	jX
2110	1.89	-5.84
2114	1.87	-5.80
2118	1.85	-5.76
2122	1.84	-5.72
2126	1.82	-5.67
2130	1.80	-5.63
2134	1.78	-5.60
2138	1.77	-5.55
2142	1.75	-5.51
2146	1.73	-5.47
2150	1.71	-5.42
2154	1.70	-5.38
2158	1.68	-5.34
2162	1.66	-5.30
2166	1.65	-5.25
2170	1.63	-5.21



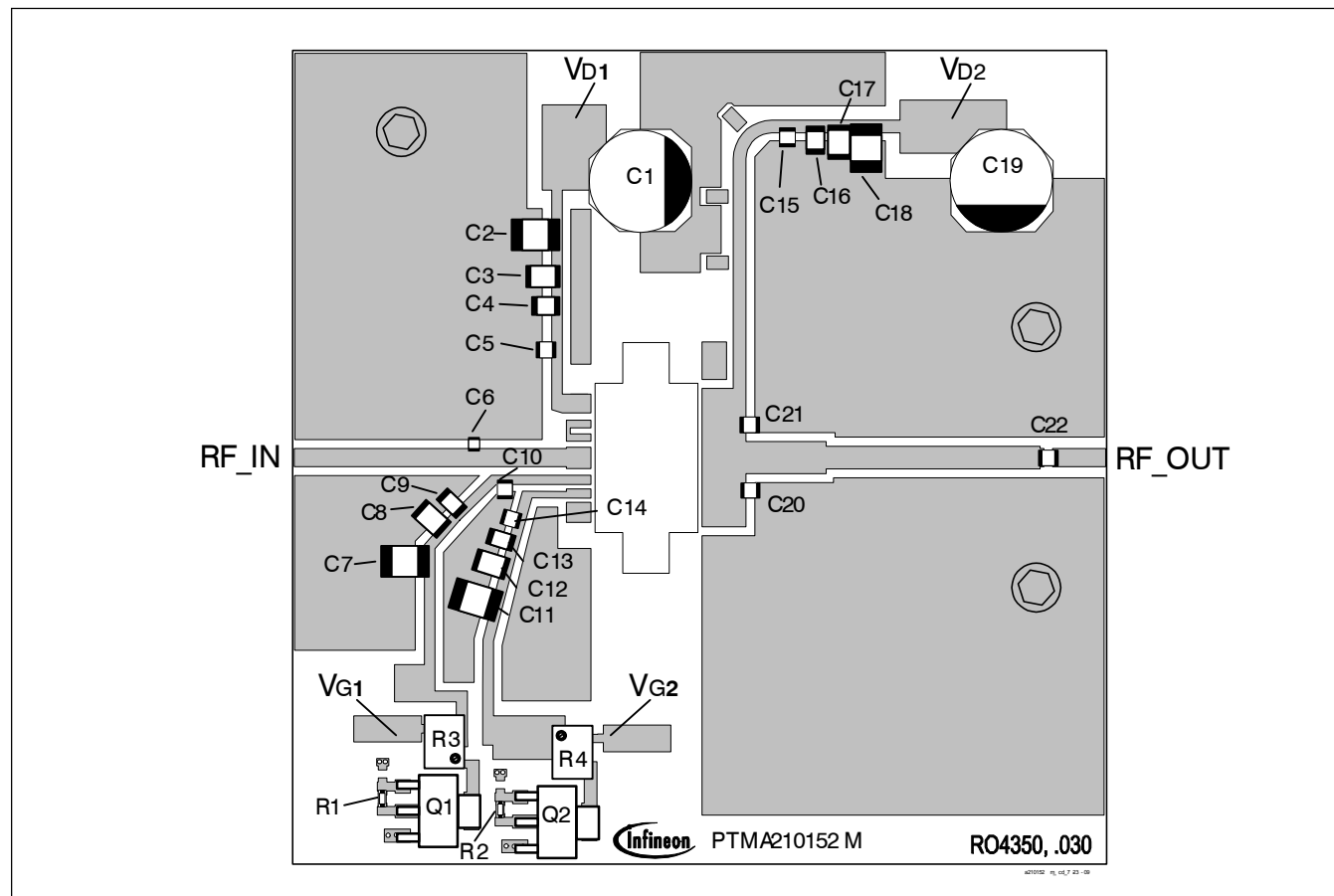
Reference Circuit ($f = 2140$ MHz)

Reference circuit schematic for $f = 2140$ MHz

Circuit Assembly Information

DUT	PTMA210152M	LDMOS IC		
PCB	LTN/PTMA210152M	0.76 mm [.030"] thick, $\epsilon_r = 3.43$	Rogers RO4350	1 oz. copper

Microstrip	Electrical Characteristics at 2140 MHz	Dimensions: L x W (mm)	Dimensions: L x W (in.)
$\ell 1$	0.228λ , 50Ω	17.48 x 1.70	0.688 x 0.067
$\ell 2$	0.125λ , 50Ω	9.40 x 1.70	0.370 x 0.067
$\ell 3$	0.054λ , 10Ω	4.09 x 12.83	0.161 x 0.505
$\ell 4$	0.340λ , 61Ω	25.91 x 1.19	1.020 x 0.047
$\ell 5$	0.005λ , 71Ω	0.38 x 0.89	0.015 x 0.035
$\ell 6$	0.005λ , 71Ω	0.38 x 0.89	0.015 x 0.035
$\ell 7$	0.100λ , 34Ω	7.47 x 3.00	0.294 x 0.118
$\ell 8$	0.271λ , 44Ω	20.40 x 2.11	0.803 x 0.083
$\ell 9$	0.066λ , 50Ω	4.95 x 1.70	0.195 x 0.067

Reference Circuit ($f = 2140$ MHz) (cont.)

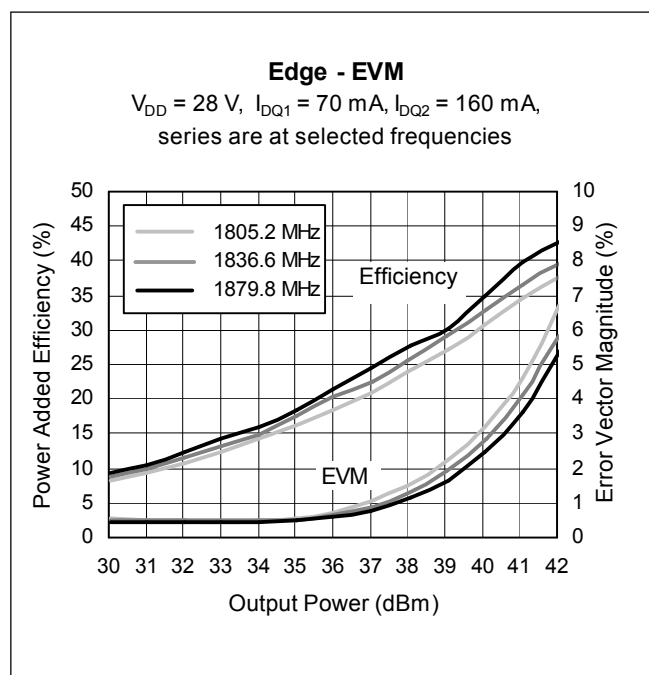
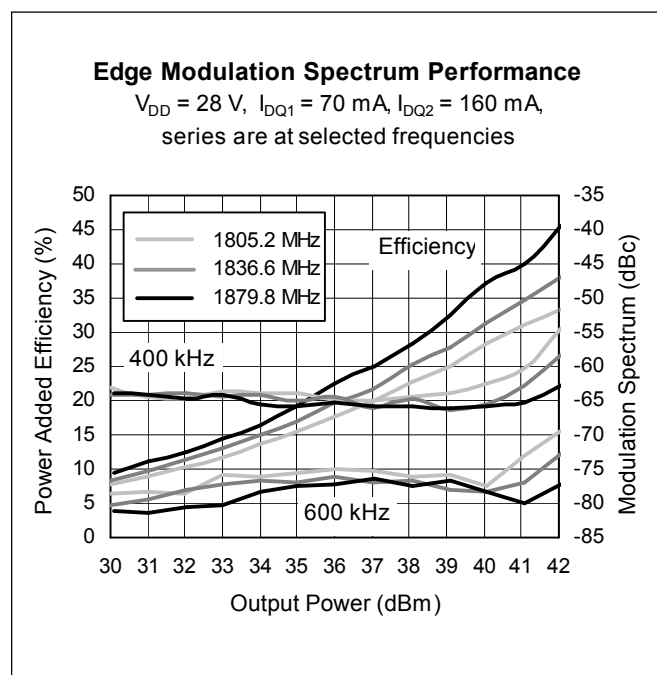
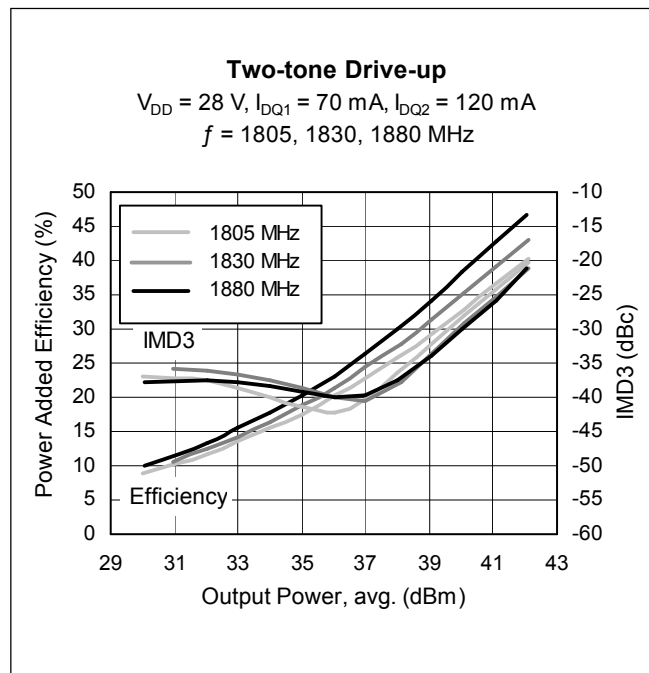
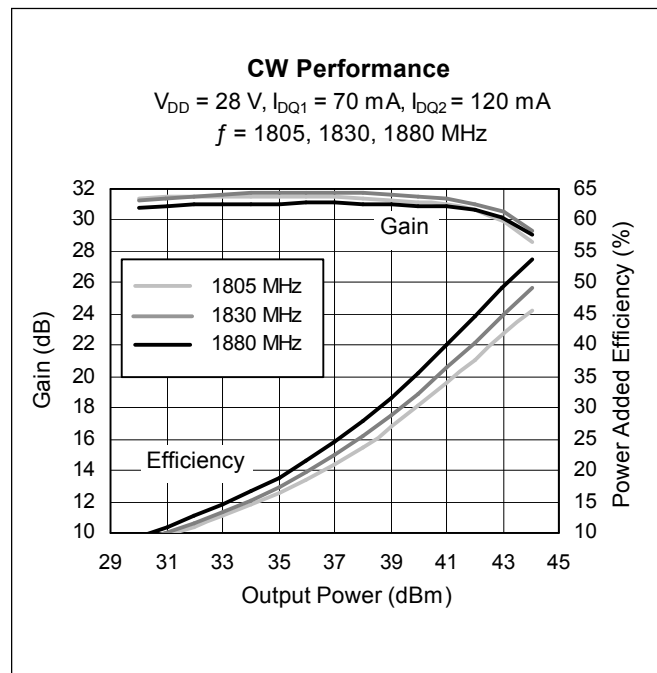


Reference circuit assembly diagram (not to scale)*

Component	Description	Suggested Manufacturer	P/N or Comment
C3, C8, C12, C17	Ceramic capacitor, 1 μ F	Digi-Key	445-1411-2-ND
C4, C9, C13, C16	Capacitor, 0.1 μ F	Digi-Key	PCC104BCT-ND
C2, C7, C11, C18	Tantalum capacitor, 10 μ F, 50 V	Digi-Key	P5571-ND
C1, C19	Electrolytic capacitor, 100 μ F, 50 V	Digi-Key	PCE3718CT-ND
C6	Ceramic capacitor, 0.5 pF	ATC	600S 0R5 CT
C20	Ceramic capacitor, 2.2 pF	ATC	600S 2R2 CT
C21	Ceramic capacitor, 1.0 pF	ATC	600S 1R0 CT
C5, C10, C14, C15, C22	Ceramic capacitor, 12 pF	ATC	600S 120 JT
Q1, Q2	Transistor	Infineon Technologies	BCP56
R1, R2	Chip resistor, 0 ohms	Digi-Key	P00ECT-ND
R3, R4	Potentiometer, 2 k ohms	Digi-Key	3224W-202ETR-ND

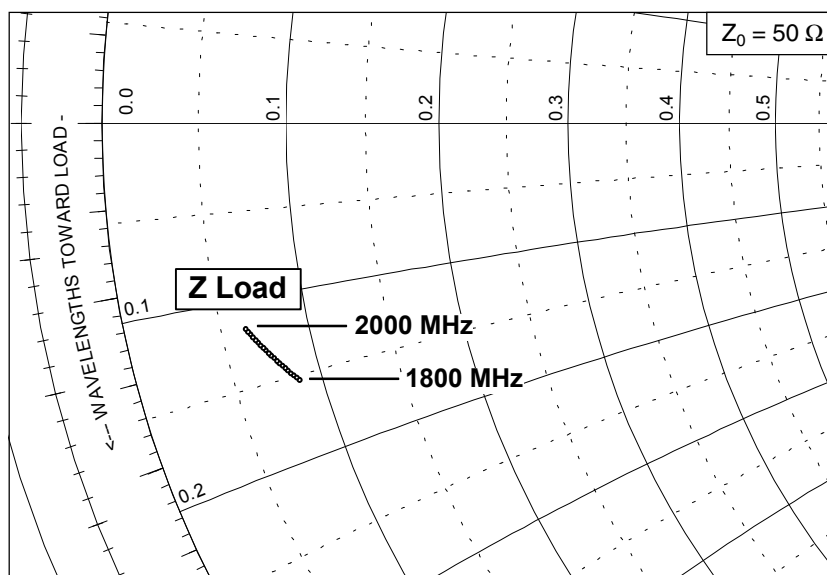
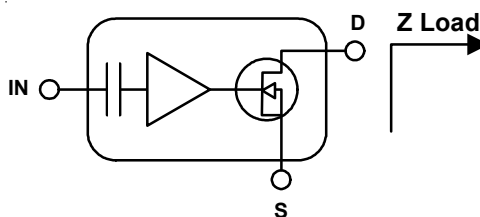
*Gerber Files for this circuit available on request

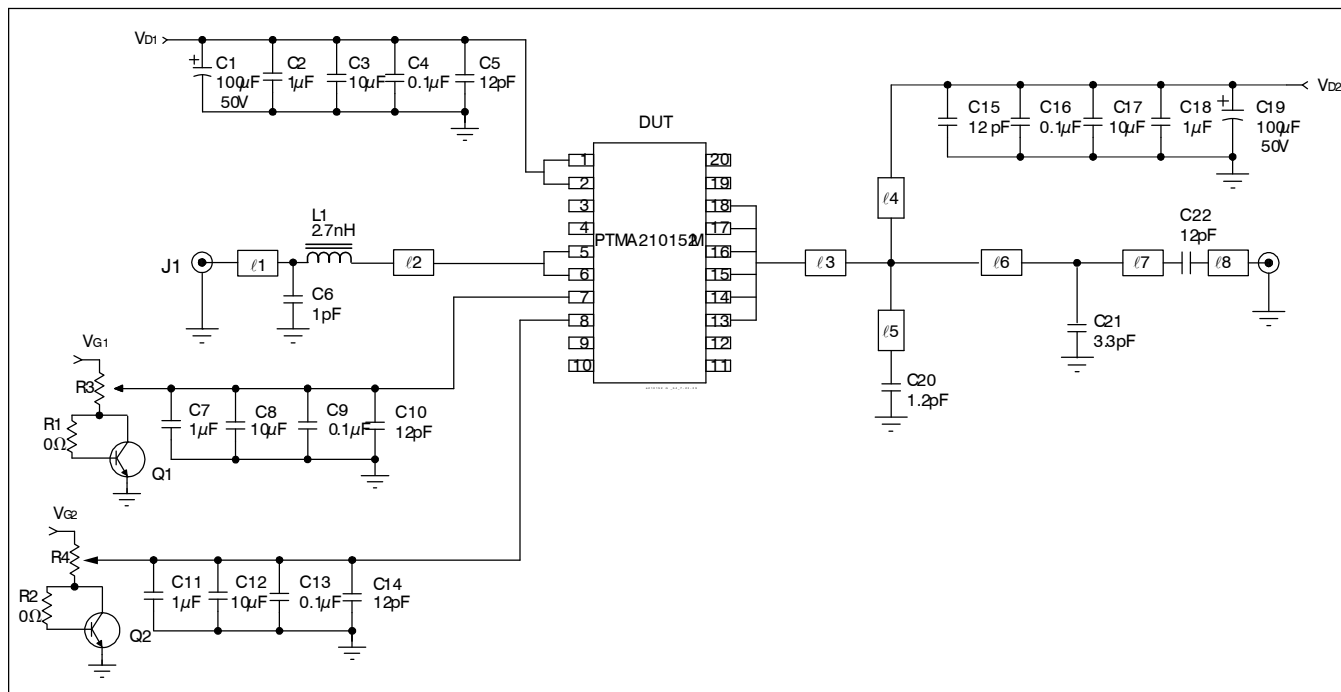
Typical Performance at 1840 MHz (data taken in Infineon test fixture)



Broadband Circuit Impedance (1840 MHz test circuit)

Frequency	Z Load W	
	R	jX
1800	4.34	-7.66
1810	4.28	-7.57
1820	4.21	-7.48
1830	4.15	-7.40
1840	4.09	-7.30
1850	4.03	-7.21
1860	3.96	-7.12
1870	3.90	-7.03
1880	3.85	-6.94
1890	3.79	-6.85
1900	3.73	-6.76
1910	3.67	-6.67
1920	3.62	-6.57
1930	3.56	-6.48
1940	3.50	-6.39
1950	3.45	-6.30
1960	3.40	-6.21
1970	3.34	-6.11
1980	3.29	-6.02
1990	3.24	-5.93
2000	3.19	-5.84

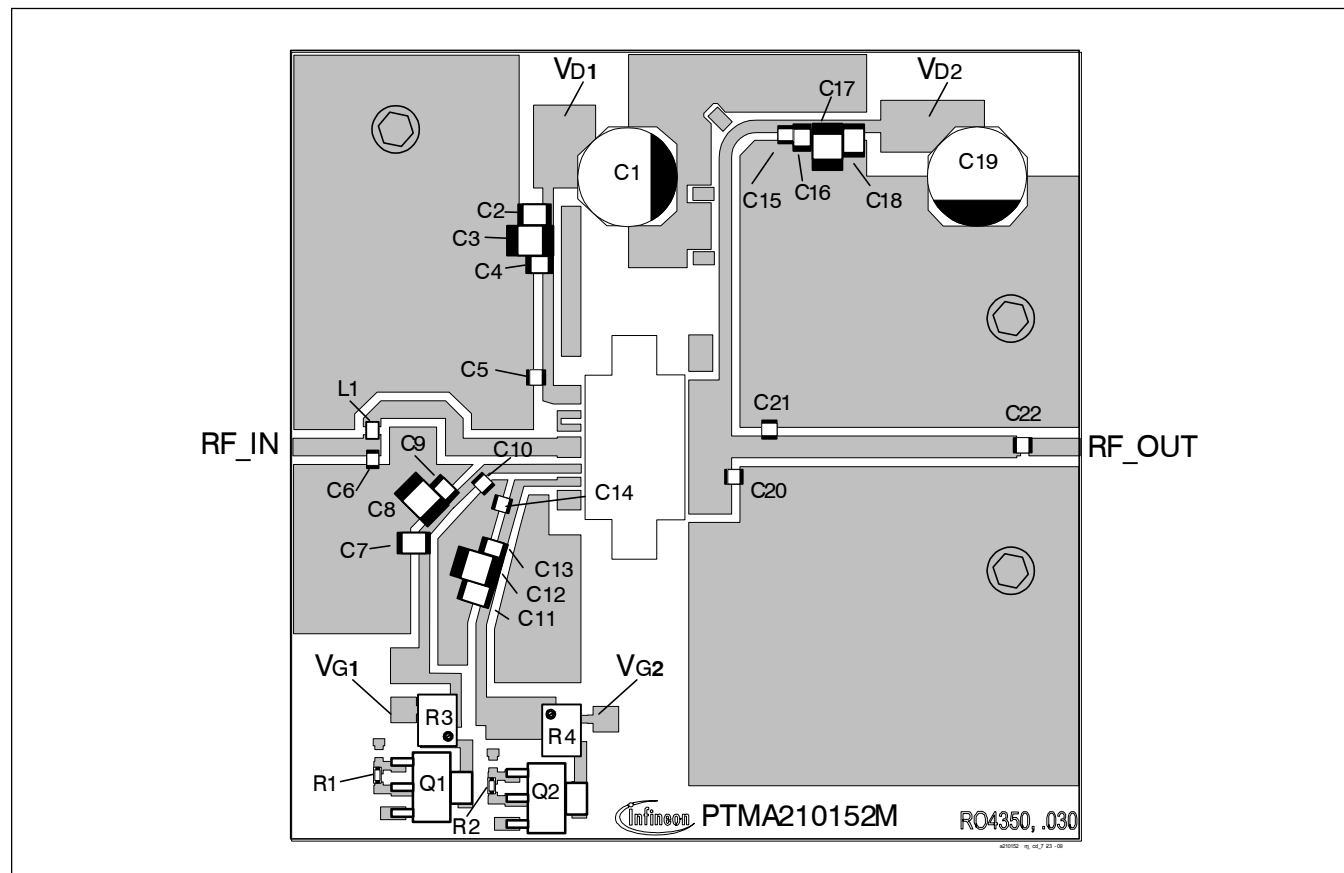


Reference Circuit ($f = 1840 \text{ MHz}$)

Reference circuit schematic for $f = 1840 \text{ MHz}$
Circuit Assembly Information

DUT	PTMA210152M	LDMOS IC		
PCB	LTN/PTMA210152M-18	0.76 mm [.030"] thick, $\epsilon_r = 3.43$	Rogers RO4350	1 oz. copper

Microstrip	Electrical Characteristics at 1840 MHz	Dimensions: L x W (mm)	Dimensions: L x W (in.)
$l1$	0.135λ , 50Ω	7.59 x 1.70	0.299 x 0.067
$l2$	0.438λ , 50Ω	24.66 x 1.70	0.971 x 0.067
$l3$	0.073λ , 10Ω	4.09 x 12.83	0.161 x 0.505
$l4$	0.461λ , 61Ω	25.91 x 1.19	1.020 x 0.047
$l5$	0.0068λ , 71Ω	0.38 x 0.89	0.015 x 0.035
$l6$	0.0307λ , 44Ω	1.73 x 2.08	0.068 x 0.082
$l7$	0.465λ , 44Ω	26.16 x 2.08	1.030 x 0.082
$l8$	0.0881λ , 50Ω	4.95 x 1.70	0.195 x 0.067

Reference Circuit ($f = 1840$ MHz) (cont.)



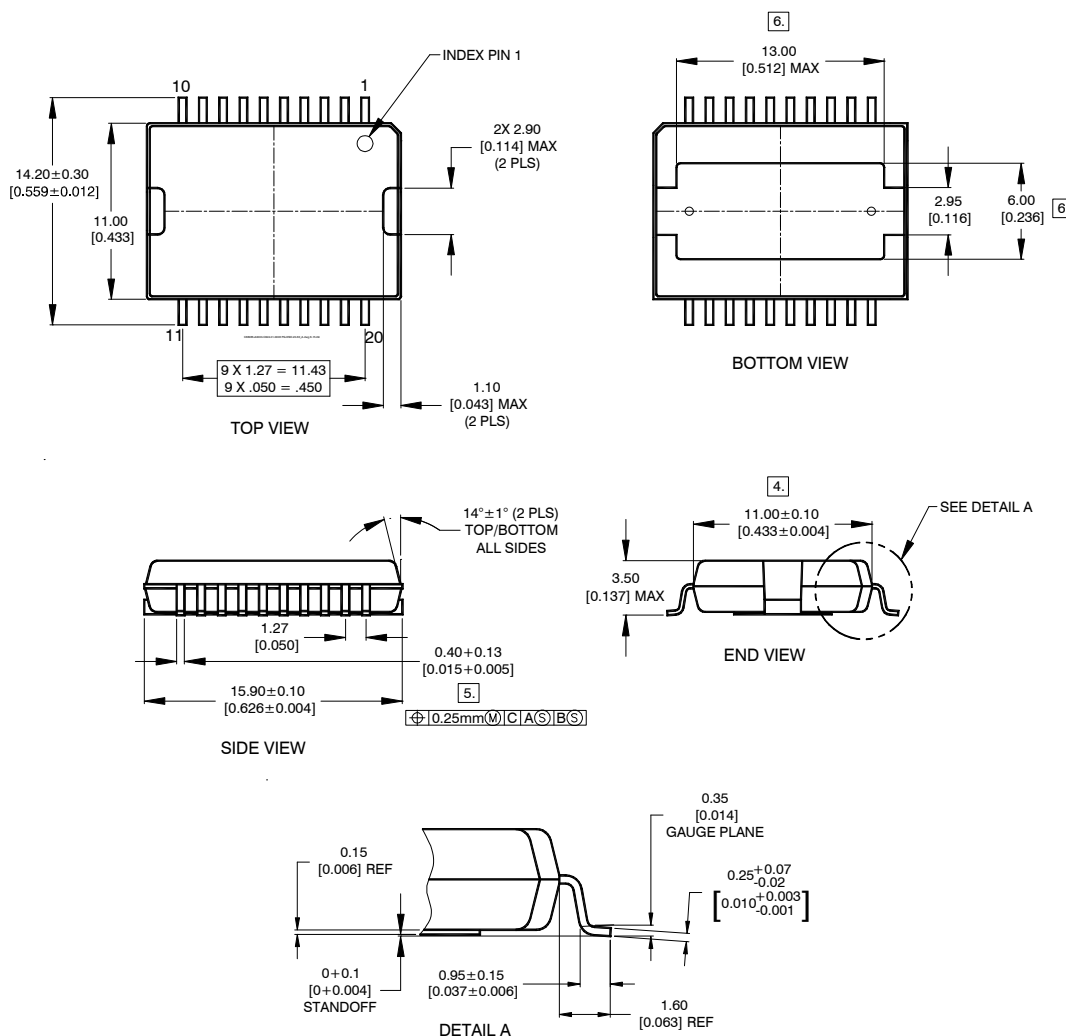
Reference circuit assembly diagram (not to scale)*

Component	Description	Suggested Manufacturer	P/N or Comment
C3, C8, C12, C17	Ceramic capacitor, 1 μ F	Digi-Key	445-1411-2-ND
C4, C9, C13, C16	Capacitor, 0.1 μ F	Digi-Key	PCC104BCT-ND
C2, C7, C11, C18	Tantalum capacitor, 10 μ F, 50 V	Digi-Key	P5571-ND
C1, C19	Electrolytic capacitor, 100 μ F, 50 V	Digi-Key	PCE3718CT-ND
C6	Ceramic capacitor, 1.0 pF	ATC	600S 1R0 CT
C20	Ceramic capacitor, 1.2 pF	ATC	600S 1R2 CT
C21	Ceramic capacitor, 3.3 pF	ATC	600S 3R3 CT
C5, C10, C14, C15, C22	Ceramic capacitor, 12 pF	ATC	600S 120 JT
Q1, Q2	Transistor	Infineon Technologies	BCP56
R1, R2	Chip resistor, 0 ohms	Digi-Key	P00ECT-ND
R3, R4	Potentiometer, 2 k ohms	Digi-Key	3224W-202ETR-ND
L1	Inductor, 2.7 nH	Digi-Key	PCD1287CT-ND

*Gerber Files for this circuit available on request

Package Specifications

Package PG-DSO-20-63 Outline

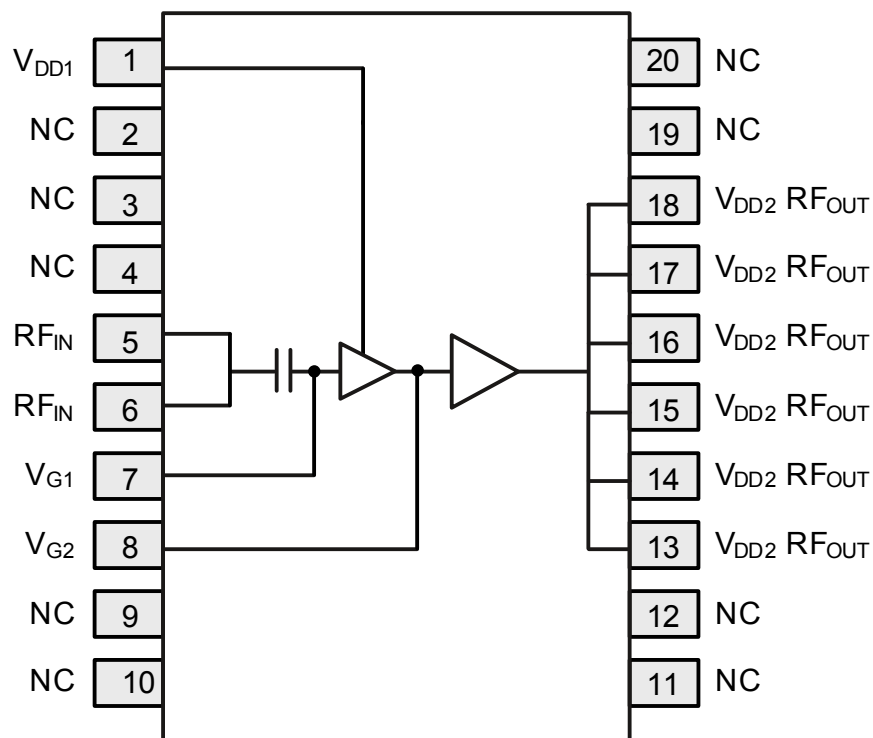


Notes: Unless otherwise specified

1. Interpret dimensions and tolerances per ASME Y14.5M-1994.
2. Package dimensions: 11.0 mm by 15.9 mm by 3.35 mm.
3. JEDEC drawing number: MO-166.
4. Does not include plastic or metal protrusion of 0.15 mm max per side.
5. Does not include dambar protrusion; maximum allowable dambar protrusion shall be 0.08 mm.
6. Bottom metallization.

Find the latest and most complete information about products and packaging at the Infineon Internet page
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Pinout Diagram



Source: Plated copper heatslug on backside of package

Find the latest and most complete information about products and packaging at the Infineon Internet page <http://www.infineon.com/rfpower>

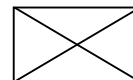
Page	Subjects (major changes since last revision)
4-6, 9-10	changed headings

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